

isc Silicon NPN Power Transistor

INCHANGE SEMICONDUCTOR

2SD2151

DESCRIPTION

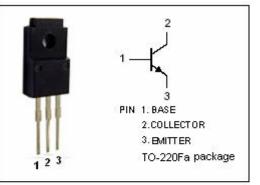
- Low Collector Saturation Voltage
 - : V_{CE(sat)}= 0.5V(Max)@ I_C= 6A
- Collector-Emitter Breakdown Voltage-: V_{(BR)CEO}= 80V (Min)
- Good Linearity of hFE
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

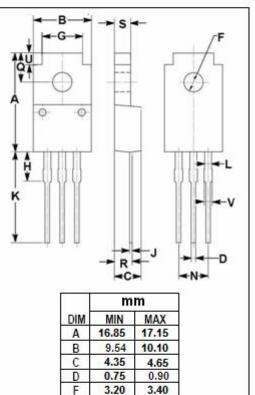
APPLICATIONS

· Designed for power switching applications.

SYMBOL	PARAMETER	VALUE	UNIT	
V _{CBO}	Collector-Base Voltage	130	v	
Vceo	Collector-Emitter Voltage	80	v	
V_{EBO}	Emitter-Base Voltage	7	V	
lc	Collector Current-Continuous	10	А	
I _{CM}	Collector Current-Peak	20	A	
Pc	Collector Power Dissipation @ T_C =25 °C	30	w	
	Collector Power Dissipation @ T _a =25°C	2		
TJ	Junction Temperature	150	°C	
T _{stg}	Storage Temperature Range	-55~150	°C	

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)





7.20

4.20

0.75

13.80

1.30

5.15

R 2.55 3.25 S 2.70 2.90 U 1.75 2.05 V 1.30 1.50

G

Н

J

K

Ν

Q

6.90 3.80

0.45

13.35

1.10

4.98

4.85

isc website: www.iscsemi.com



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ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA; I _B = 0	80			v
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 6A; I _B = 0.3A			0.5	v
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = 10A; I _B = 1A			1.5	V
V _{BE(sat)-1}	Base-Emitter Saturation Voltage	I _C = 6A; I _B = 0.3A			1.5	V
V _{BE(sat)-2}	Base-Emitter Saturation Voltage	Ic= 10A; I _B = 1A			2.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 100V; I _E = 0			10	μA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			50	μ Α
hfe-1	DC Current Gain	Ic= 0.1A; Vce= 2V	45			
h _{FE-2}	DC Current Gain	I _C = 3A; V _{CE} = 2V	90		260	
h _{FE-3}	DC Current Gain	I _C = 6A; V _{CE} = 2V	30			
f⊤	Current-Gain—Bandwidth Product	Ic= 0.5A; V _{CE} = 10V; f= 10MHz		20		MHz

• h_{FE-2} classifications

Q	Р	
90-180	130-260	

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